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[AMENDMENT UNDER 37 C.F.R. § 1.11]
U.S. APPLN. NO.: 09/670,616]

extensively used. More preferably, a material such as a silicone resin, a polyamide resin, a polyamideimide resin, a polyimide resin, etc. may be used. These materials have high heat-resistant properties and exhibit excellent performance in surface properties magnetostatic properties. Coating thickness of the flattening layer is preferably 0.1 - 5.0 μm , or more preferably 0.5 - 3.0 μm , or most preferably 0.8 - 2.0 μm .

IN THE CLAIMS:

Please cancel claims 3, 7, 11 and 17 without prejudice or disclaimer.

Claims 2, 4-6, 8-10, 12-16 and 18-20 are amended as follows:

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2. (Amended) A floppy disk according to claim 1, wherein there is provided a flattening layer, comprising a heat-resistant polymer selected from the group consisting of a silicone resin, a polyamide resin, a polyamideimide resin, and a polyimide resin, on the flexible nonmagnetic support member.

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4. (Amended) A floppy disk according to claim 2, wherein the thickness of the flattening layer is within the range of 0.1 - 5 μm .

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5. (Amended) A floppy disk according to claim 1, wherein the thickness of the flexible support member is within the range of 30 - 100 μm .

6. (Amended) A floppy disk according to claim 2, wherein the thickness of the flexible support member is within the range of 30 - 100 μm .

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8. (Amended) A floppy disk according to claim 4, wherein the thickness of the flexible support member is within the range of 30 - 100 μm .

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9. (Amended) A floppy disk according to claim 1, wherein a Co-Cr alloy with a Cr concentration within the range of 10 - 30 atom % is used for the magnetic layer.

10. (Amended) A floppy disk according to claim 2, wherein a Co-Cr alloy with a Cr concentration within the range of 10 - 30 atom % is used for the magnetic layer.

12. (Amended) A floppy disk according to claim 4, wherein a Co-Cr alloy with a Cr concentration within the range of 10 - 30 atom % is used for the magnetic layer.

13. (Amended) A floppy disk according to claim 5, wherein a Co-Cr alloy with a Cr concentration within the range of 10 - 30 atom % is used for the magnetic layer.

14. (Amended) A floppy disk according to claim 6, wherein a Co-Cr alloy with a Cr concentration within the range of 10 - 30 atom % is used for the magnetic layer.

15. (Amended) A floppy disk according to claim 1, wherein a Cr alloy with a Cr concentration within the range of 77 - 100 atom % is used as the primer layer.

16. (Amended) A floppy disk according to claim 2, wherein a Cr alloy with a Cr concentration within the range of 77 - 100 atom % is used as the primer layer.

18. (Amended) A floppy disk according to claim 4, wherein a Cr alloy with a Cr concentration within the range of 77 - 100 atom % is used as the primer layer.

19. (Amended) A floppy disk according to claim 5, wherein a Cr alloy with a Cr concentration within the range of 77 - 100 atom % is used as the primer layer.

20. (Amended) A floppy disk, comprising a flattening layer with a thickness of 0.1 - 5 μm , a seed layer, a nonmagnetic primer layer containing a Cr alloy with a Cr concentration of 77 - 100 atom %, a magnetic layer containing a Co-Cr alloy with a Cr concentration of 10 - 30